

**N-Ch MOSFET** 

# **General Description**

The WSR170N04G uses SGT and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

#### **Features**

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

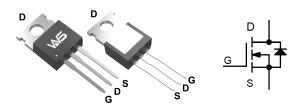
## **Product Summery**

BVDSS	RDSON	ID		
40V	3mΩ	170A		

# **Application**

- Load switch
- Battery protection
- Uninterruptible power supply

## **TO-220AB Pin Configuration**



## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
$V_{DS}$	Drain-Source Voltage	40	V	
$V_{GS}$	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	170	Α	
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	135	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	800	Α	
EAS	Single Pulse Avalanche Energy <sup>3</sup>	450	mJ	
P <sub>D</sub> @T <sub>C</sub> =25℃	Total Power Dissipation <sup>4</sup>	185	W	
T <sub>J</sub> T <sub>STG</sub>	Operating Junction Temperature Range -55 to 150		$^{\circ}$	

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>		50	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		0.7	°C/W

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# Electrical Characteristics (T<sub>J</sub>=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V , $I_D$ =250uA	40			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25℃, I <sub>D</sub> =1mA		0.057		V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =20A		1.9	3	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage		1.2	1.8	2.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	V <sub>GS</sub> -V <sub>DS</sub> , I <sub>D</sub> -250uA		-5.68		mV/℃
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =40V , $V_{GS}$ =0V , $T_J$ =25 $^{\circ}$ C			1	uA
DSS		$V_{DS}$ =40V , $V_{GS}$ =0V , $T_J$ =55 $^{\circ}$ C			5	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}$ =0V			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =15A		50		S
$R_g$	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.0		Ω
$Q_{g}$	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V , V <sub>GS</sub> =10V , I <sub>D</sub> =20A		45		
$Q_gs$	Gate-Source Charge			12		nC
$Q_gd$	Gate-Drain Charge			18		
$T_{d(on)}$	Turn-On Delay Time	$\begin{array}{c} \  \   \  \   \  \   \  \   \   $		19		
Tr	Rise Time			10		- ns
$T_{d(off)}$	Turn-Off Delay Time			59		
$T_f$	Fall Time			32		
C <sub>iss</sub>	Input Capacitance			3950		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =20V , V <sub>GS</sub> =0V , f=1MHz		1120		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			98		

### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			170	Α
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>				800	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25℃			1.2	V
t <sub>rr</sub>	Reverse Recovery Time	IF=20A ,dI/dt=100A/μs,TJ=25℃		35		nS
Q <sub>rr</sub>	Reverse Recovery Charge			56		nC

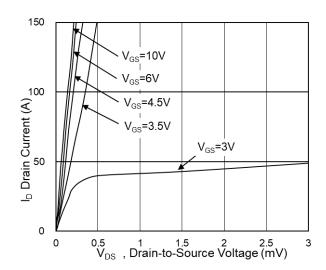
### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width ≤ 300 $\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition: Tj=25  $^{\circ}$ C,V<sub>DD</sub>=20V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$



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# **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

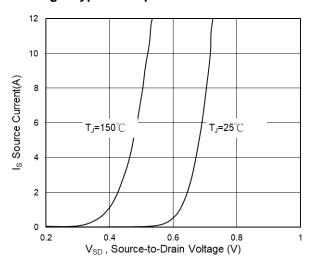


Fig.3 Source Drain Forward Characteristics

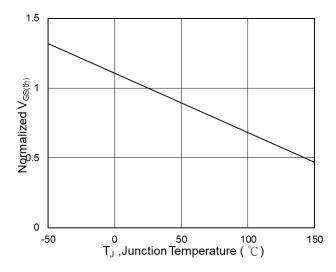


Fig.5 Normalized V<sub>GS(th)</sub> vs T<sub>J</sub>

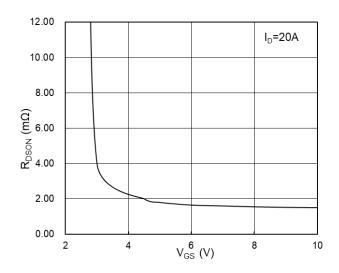


Fig.2 On-Resistance vs G-S Voltage

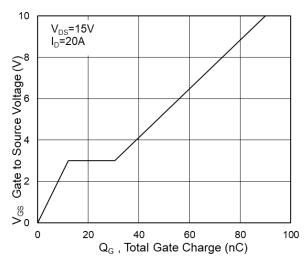


Fig.4 Gate-Charge Characteristics

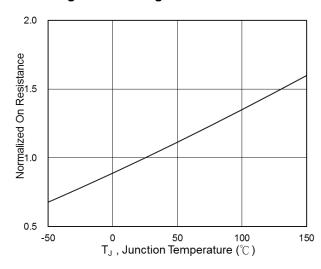
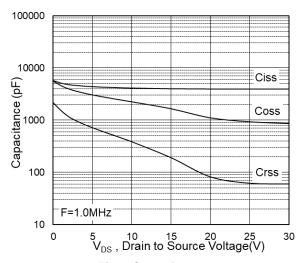


Fig.6 Normalized R<sub>DSON</sub> vs T<sub>J</sub>







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Fig.7 Capacitance

Fig.8 Safe Operating Area

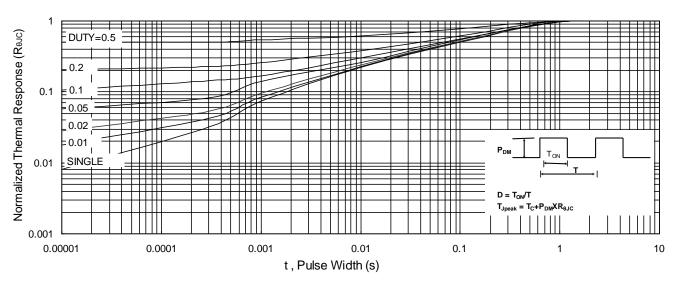
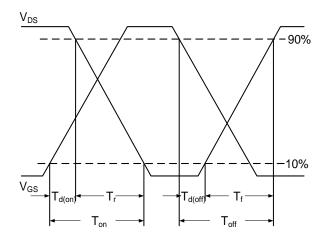


Fig.9 Normalized Maximum Transient Thermal Impedance



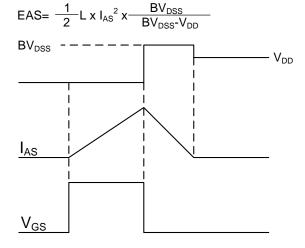


Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform



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